TECH PUBLIC
台舟电子

FDN340P

P-Channel Mosfet

www.sot23.com.tw

Product Summary

- V_{DS} = -20V,I_D =-2A

$R_{DS(ON)}$ < 70mΩ @ V_{GS}=-4.5V

$R_{DS(ON)}$ < 110mΩ @ V_{GS}=-2.5V

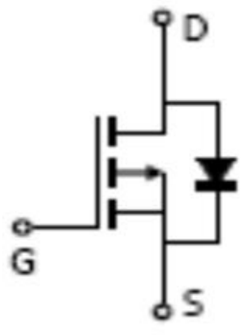
Application

- Load/Power Switching
- Interfacing Switching
- Logic Level Shift

Package and Pin Configuration

SOT-23

Circuit diagram



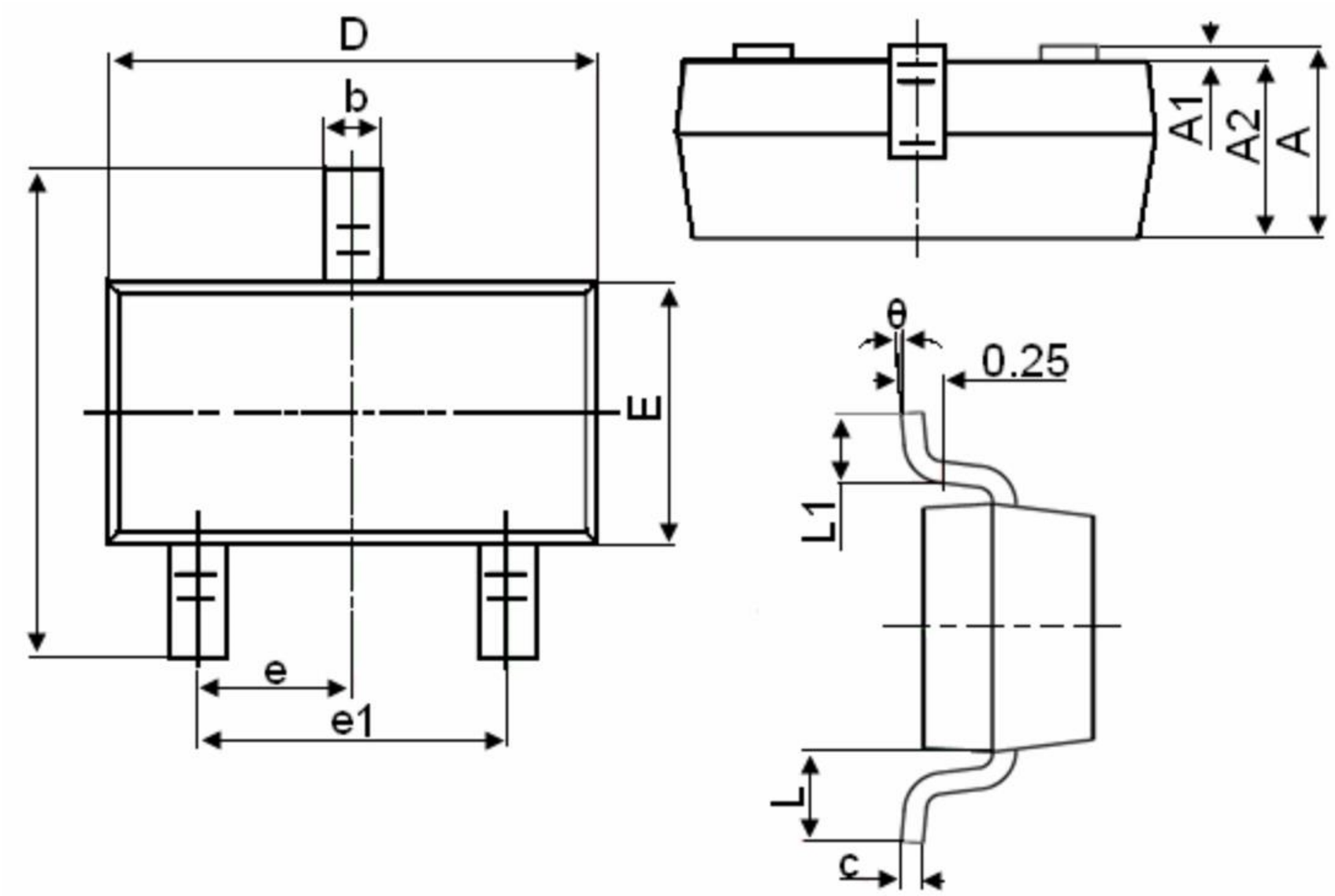
Absolute Maximum Ratings (T_A=25°C unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	VDS	-20	V
Gate-Source Voltage	VGS	±8	
Continuous Drain Current	ID	-2	A
Pulsed Diode Curren	IDM	-10	
Power Dissipation	PD	1.1	W
Thermal Resistance from Junction to Ambient (t≤10s)	RθJA	250	℃/W
Operating Junction	TJ	150	℃
Storage Temperature	TSTG	-55~+150	℃

Electrical Characteristics (T_A = 25°C unless otherwise noted)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Static						
Drain-source breakdown voltage	V(BR)DSS	VGS = 0V, ID = -250μA	-20			V
Gate-source threshold voltage	VGS(th)	VDS =VGS, ID = -250μA	-0.4		-1.5	V
Gate-source leakage	IGSS	VDS =0V, VGS = ±8V			±100	nA
Zero gate voltage drain current	IDSS	VDS = -16V, VGS =0V			-1	μA
Drain-source on-state resistancea	RDS(on)	VGS = -4.5V, ID = -2A		52	70	mΩ
		VGS = -2.5V, ID = -1.7A		78	110	mΩ
		VGS = -1.8V, ID = -1.2A			210	mΩ
Forward transconductancea	gfs	VDS = -4.5V, ID = -2A		8		S
Diode forward voltage	VSD	IS= -1A,VGS=0V		-0.8	-1.2	V
Dynamic						
Input capacitance	Ciss	VDS = -10V,VGS =0V, f=1MHz		600		pF
Output capacitance	Coss			175		pF
Reverse transfer capacitanceb	Crss			80		pF
Total gate charge	Qg	VDS = -10V,VGS = -4.5V, ID = -2A		8		nC
Gate-source charge	Qgs			1.3		nC
Gate-drain charge	Qgd			2.2		nC
Gate resistance	Rg	f=1MHz	0.5		3.2	Ω
Switchingbtr						
Turn-on delay time	td(on)	VDS= -10V RL=3.5Ω, ID ≈ -1A, VGEN= -4.5V,Rg=3Ω		6		ns
Rise time	tr			9		ns
Turn-off delay time	td(off)			31		ns
Fall time	tf			26		ns
Drain-source body diode characteristicstr						
Continuous Source-Drain Diode Current	IS	Tc=25℃			-1.2	A
Pulsed Diode forward Curren	ISM				-10	A

SOT-23 Package Information



Symbol	Dimensions in Millimeters	
	MIN.	MAX.
A	0.900	1.150
A1	0.000	0.100
A2	0.900	1.050
b	0.300	0.500
c	0.080	0.150
D	2.800	3.000
E	1.200	1.400
E1	2.250	2.550
e	0.950TYP	
e1	1.800	2.000
L	0.550REF	
L1	0.300	0.500
θ	0°	8°

X-ON Electronics

Largest Supplier of Electrical and Electronic Components

Click to view similar products for MOSFET ***category:***

Click to view products by TECH PUBLIC ***manufacturer:***

Other Similar products are found below :

614233C 648584F NTNS3A92PZT5G IRFD120 IRFF430 JANTX2N5237 2N7000 2SK2464-TL-E FCA20N60_F109 FDZ595PZ AOD464 2SK2267(Q) 2SK2545(Q,T) 405094E 423220D MIC4420CM-TR VN1206L 614234A 715780A SSM6J414TU,LF(T 751625C IPP60R600P6XKSA1 RJK60S5DPK-M0#T0 BSC884N03MS G BSF024N03LT3 G PSMN4R2-30MLD TK31J60W5,S1VQ(O 2SK2614(TE16L1,Q) DMN1017UCP3-7 EFC2J004NUZTDG FCAB21350L1 P85W28HP2F-7071 DMN1053UCP4-7 NTE2384 NTE2969 NTE6400A DMN2080UCB4-7 DMN61D9UWQ-13 US6M2GTR DMN31D5UDJ-7 SSM6P54TU,LF DMP22D4UFO-7B IPS60R3K4CEAKMA1 DMN1006UCA6-7 DMN16M9UCA6-7 STF5N65M6 STU5N65M6 C3M0021120D DMN13M9UCA6-7 BSS340NWH6327XTSA1